



100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(ON) Max	I _D Tc = +25°C
100V	14mΩ @ V _{GS} = 10V	59A
1000	20mΩ @ V _{GS} = 6V	50A

Description

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_g –Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH10H015SK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

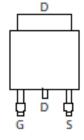
Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)

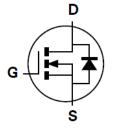








Pin Out Top View



Equivalent Circuit

Ordering Information (Note 4)

- 7			
	Part Number	Case	Packaging
	DMTH10H015SK3Q-13	TO252 (DPAK)	2500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



DII = Manufacturer's Marking
TH1H015SK = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	100	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current, V _{GS} = 10V		I _D 59	59 42	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	T _C = +100°C	Ірм	235	A
Maximum Continuous Body Diode Forward Current (Note 6)	Is	2.7	A	
Pulsed Body Diode Forward Current (10μs Pulse, T _C = +25°C, Packa	I _{SM}	235	Α	
Avalanche Current, L = 0.1mH	I _{AS}	15.8	Α	
Avalanche Energy, L = 0.1mH	Eas	12.5	mJ	
Avalanche Current, L = 3mH (Note 8)	las	7.5	Α	
Avalanche Energy, L = 3mH (Note 8)	E _{AS}	85	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	75	°C/W
Total Power Dissipation (Note 6)		P _D	3.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction to Case		R ₀ JC	2	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

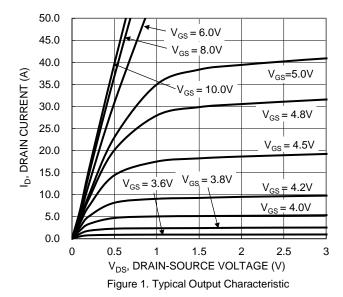
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
Characteristic Symbol Min Typ Max Unit Test Condition OFF CHARACTERISTICS (Note 7)							
, , , ,	D\/	100	l	<u> </u>	\/	N/ 01/ I= 4 m A	
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_		1	μΑ	$V_{DS} = 80V$, $V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	—	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2		4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	11.1	14	mΩ	$V_{GS} = 10V, I_{D} = 20A$	
Static Dialif-Source Off-Resistance	RDS(ON)		14.7	20	11177	$V_{GS} = 6V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	_	0.86	1.3	V	V _G S = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	2343	_		V _{DS} = 50V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	487	_	pF		
Reverse Transfer Capacitance	Crss	_	26	_			
Gate Resistance	Rg	_	0.69	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	30.1	_		501/ 1- 404	
Gate-Source Charge	Qgs	_	7.5	_	nC	$V_{DD} = 50V, I_{D} = 10A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_{gd}	_	6.5	_		VGS = 10V	
Turn-On Delay Time	tD(ON)	_	9.8				
Turn-On Rise Time	t _R	_	7.8	_	200	$V_{DD} = 50V, V_{GS} = 10V,$	
Turn-Off Delay Time	tD(OFF)	_	22.5		ns	$I_D=10A,\ R_g=6\Omega$	
Turn-Off Fall Time	t _F	_	9.6	_			
Reverse Recovery Time	trr	_	43	_	ns	I_ 400 di/dt 4000/	
Reverse Recovery Charge	Q_{RR}	_	65.1	_	nC	I _F = 10A, di/dt = 100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:







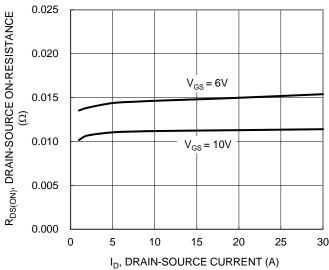


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

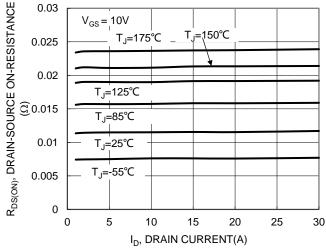
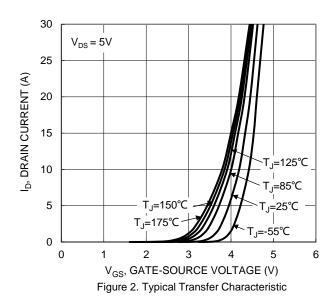
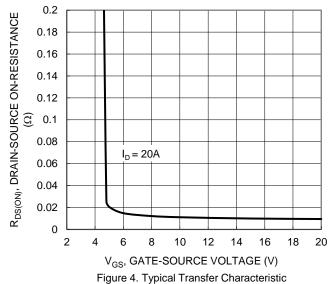


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





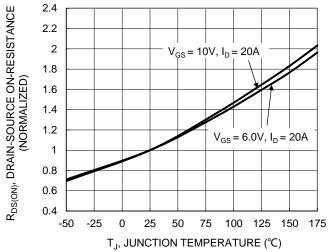


Figure 6. On-Resistance Variation with Temperature





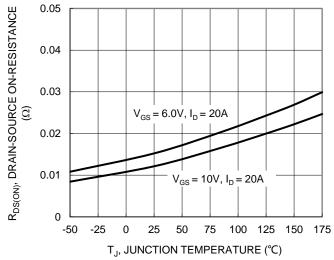


Figure 7. On-Resistance Variation with Temperature

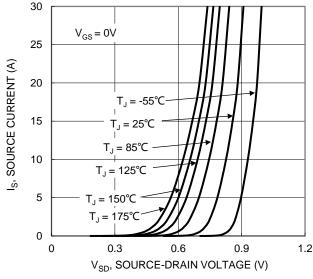


Figure 9. Diode Forward Voltage vs. Current

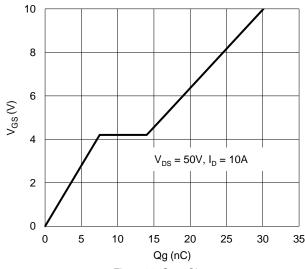


Figure 11. Gate Charge

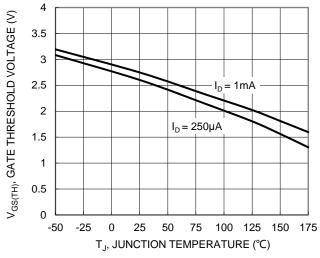


Figure 8. Gate Threshold Variation vs. JunctionTemperature

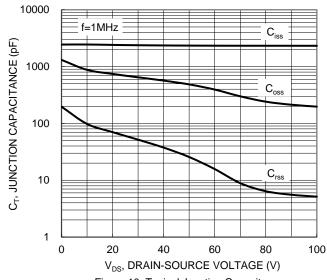


Figure 10. Typical Junction Capacitance

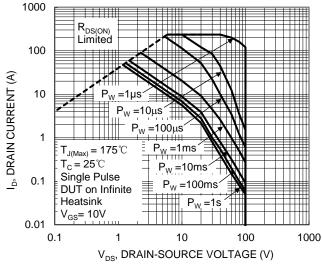


Figure 12. SOA, Safe Operation Area



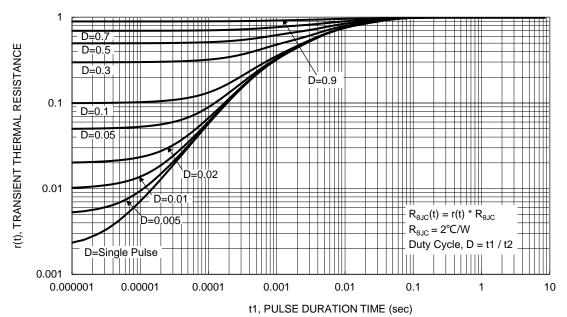


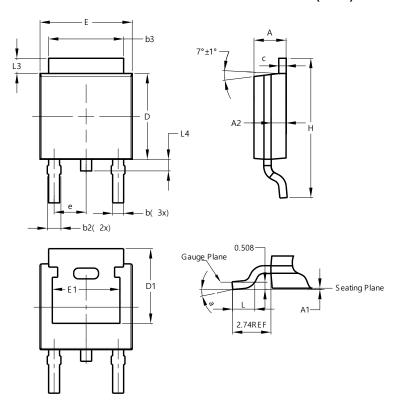
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

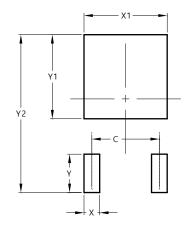


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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